

P-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)		
- 100	$0.037 \text{ at V}_{GS} = -10 \text{ V}$	- 40	35		
- 100	0.042 at $V_{GS} = -4.5 \text{ V}$	- 30	33		

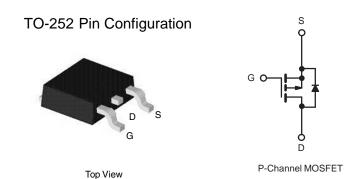
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Power Switch
- DC/DC Converters



ABSOLUTE MAXIMUM RATINGS T _C = 25 °C, unless otherwise noted						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V _{DS}	- 100	V			
Gate-Source Voltage	V _{GS}	± 20	V			
Continuous Drain Current (T _{.I} = 150 °C)	T _C = 25 °C	1-	- 40			
Continuous Diam Current (1) = 130 C)	T _C = 70 °C	l _D	- 35	A		
Pulsed Drain Current	I _{DM}	- 120				
Avalanche Current	I _{AS}	- 25				
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	25.7	mJ		
	T _C = 25 °C	В	87 ^b	10/		
Maximum Power Dissipation ^a	T _A = 25 °C ^c	P _D	3.5	W		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	50	°C/W		
Junction-to-Case (Drain)	R _{thJC}	2.2			

Notes:

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When Mounted on 1" square PCB (FR-4 material).

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$				V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3.5	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA
Zero Gate Voltage Drain Current		V _{DS} = - 100 V, V _{GS} = 0 V			- 1	
	I _{DSS}	V _{DS} = - 100 V, V _{GS} = 0 V, T _J = 125 °C			- 50	μΑ
		V _{DS} = - 100 V, V _{GS} = 0 V, T _J = 150 °C			- 250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -10 \text{ V}, V_{GS} = -10 \text{ V}$	- 120			Α
David Course Co Clate Davidson	P	V _{GS} = - 10 V, I _D = - 3.6 A		0.037	0.047	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 3.4 A		0.042	0.050	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 3.6 A		17		S
Dynamic ^b						
Input Capacitance	C _{iss}			3922		pF
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = -50 \text{ V}, f = 1 \text{ MHz}$		885		
Reverse Transfer Capacitance	C _{rss}]		504		
Total Gate Charge ^c	Qg	V _{DS} = -50 V, V _{GS} = -10 V, I _D = -3.6 A		35		
				17		nC
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = -50 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -3.6 \text{ A}$		5		IIC
Gate-Drain Charge ^c	Q _{gd}			4.9		
Gate Resistance	R_g	f = 1 MHz	1.2	5.7	11.5	Ω
Turn-On Delay Time ^c	t _{d(on)}			18		
Rise Time ^c	t _r	$V_{DD} = -50 \text{ V}, R_{L} = 17.2 \Omega$		22		no
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ - 2.9 A, V_{GEN} = - 10 V, R_g = 1 Ω		49		ns
Fall Time ^c	t _f			15		
Drain-Source Body Diode Ratings ar	nd Characteri	stics T _C = 25 °C ^b				
Continuous Current	I _S				- 40	۸
Pulsed Current	I _{SM}				-120	А
Forward Voltage ^a	V _{SD}	I _F = - 2.9 A, V _{GS} = 0 V		- 0.8	- 1.5	V
Reverse Recovery Time	t _{rr}			50		ns
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = - 2.9 A, dl/dt = 100 A/μs		- 4	- 6	А
Reverse Recovery Charge	Q _{rr}	1		98	147	nC

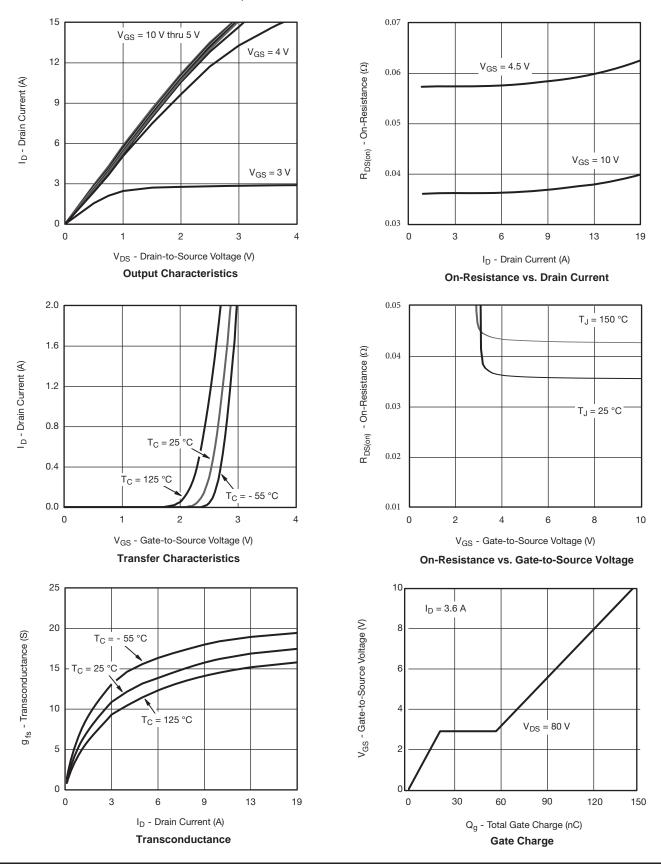
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

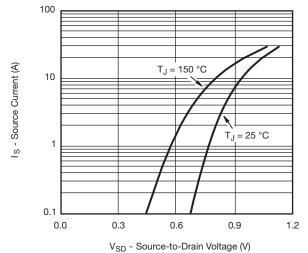


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

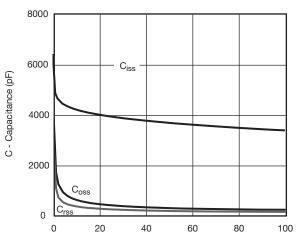




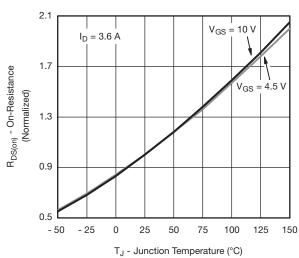
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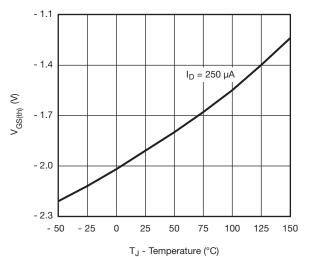
Source-Drain Diode Forward Voltage



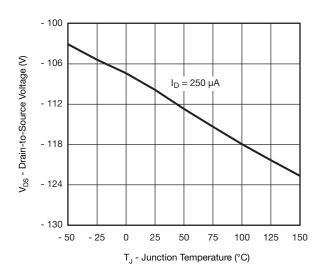
 V_{DS} - Drain-to-Source Voltage (V) $\label{eq:capacitance}$



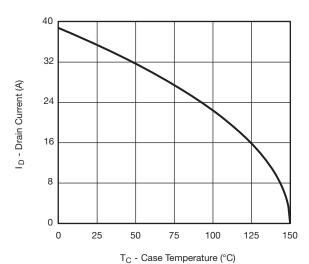
On-Resistance vs. Junction Temperature



Threshold Voltage

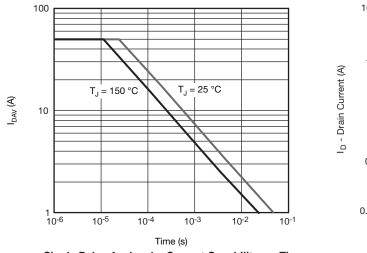


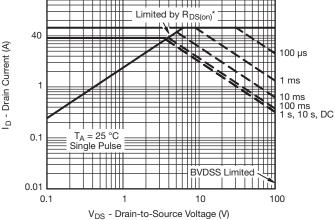
Drain Source Breakdown vs. Junction Temperature



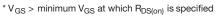
To case temperature (

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

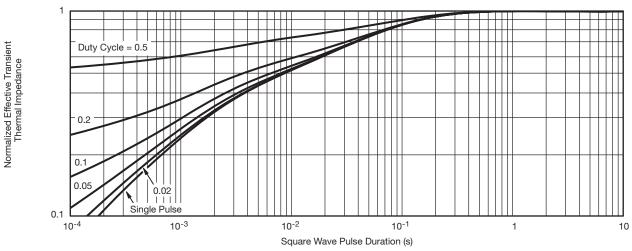




Single Pulse Avalanche Current Capability vs. Time







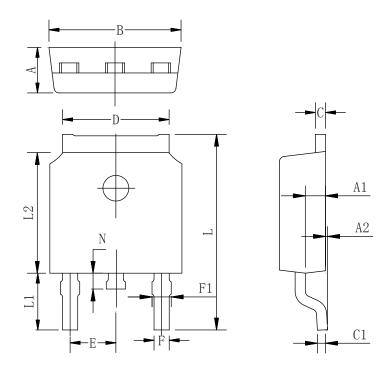
Normalized Thermal Transient Impedance, Junction-to-Case

Din-Tek

SEMICONDUCTOR



TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max
A	2.10	2.30	2.50
A1	0.88	1.01	1.16
A2	0.00	0.15	0.28
В	6.40	6.60	6.80
С	0.42	0.50	0.63
C1	0.42	0.50	0.63
D	5.08	5.32	5.65
Е	2.286 TYP		
F	0.63	0.76	0.89
F1	0.64	0.86	1.08
L	9.30	9.90	10.80
L1	2.4	2.8	3.6
L2	5.90	6.10	6.55
N	0.57	0.80	1.05





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